

Silicon PNP Power Transistors

2SB992

DESCRIPTION

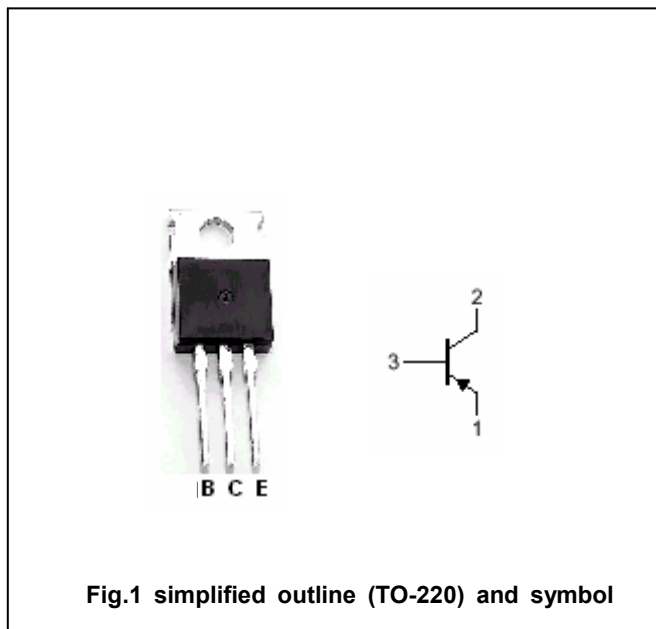
- With TO-220 package
- Low collector saturation voltage
- Large current capacity

APPLICATIONS

- Suitable for relay drivers,high-speed Inverters,converters,and other general large-current switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-100	V
V _{CEO}	Collector-emitter voltage	Open base	-80	V
V _{EBO}	Emitter-base voltage	Open collector	-7	V
I _C	Collector current		-7	A
I _{CM}	Collector current-peak		-10	A
P _C	Collector power dissipation	T _C =25°C	40	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-1mA, R _{BE} =∞	-80			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-1mA, I _E =0	-100			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1mA, I _C =0	-7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-4A; I _B =-0.4A			-0.4	V
I _{CBO}	Collector cut-off current	V _{CB} =-80V; I _E =0			-5	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-4V; I _C =0			-5	μA
h _{FE-1}	DC current gain	I _C =-1A; V _{CE} =-1V	70		240	
h _{FE-2}	DC current gain	I _C =-4A; V _{CE} =-1V	30			
f _T	Transition frequency	I _C =-1A; V _{CE} =-5V		10		MHz

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PACKAGE OUTLINE



Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)